

Notice of References Cited

Application/Control No.

09/456,873

Applicant(s)/Patent Under
Reexamination
MORI, SEIICHI

Examiner

Leonardo Andujar

Art Unit

2826

Page 1 of 1

U.S. PATENT DOCUMENTS

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification	
	A	US-5,374,847-	12-1994	Araki et al.	257	639
	B	US-5,661,056-	08-1997	Takeuchi	438	261
	C	US-5,907,183-	05-1999	Takeuchi	257	640
	D	US-5,793,081-	08-1998	Tomioka et al	257	319
	E	US- -				
	F	US- -				
	G	US- -				
	H	US- -				
	I	US- -				
	J	US- -				
	K	US- -				
	L	US- -				
	M	US- -				

FOREIGN PATENT DOCUMENTS

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Country	Name	Classification	
	N	JP-358106873-A	06-1983	Japan	Yamada	257	324
	O	- -					
	P	- -					
	Q	- -					
	R	- -					
	S	- -					
	T	- -					

NON-PATENT DOCUMENTS

*		Include as applicable: Author, Title Date, Publisher, Edition or Volume, Pertinent Pages)				
	U	Wang et al. Dual Frequency Silicon Nitride of Low Thermal Budget for Pre-Metal Dielectric Applications, 1999 IEE/SEMI Advanced Semiconductor Manufacturing Conference , 405				
	V	Klein et al., Silicon nitride PECVD at low temperature: film properties plasma analysis, 4/06/1998, Plasma Science, 1998. 25th anniversary. IEEE 215				
	W					
	X					

*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)
Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.